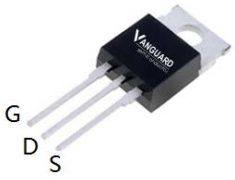
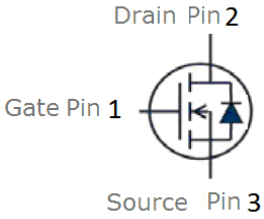
Features

- N-Channel，5V Logic Level Control
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5V
- 100% Avalanche test
- Pb-free lead plating; RoHS compliant

V_{DS}	40	V
$R_{DS(on),TYP}$@ V_{GS}=10V	2.5	mΩ
$R_{DS(on),TYP}$@ V_{GS}=4.5V	3.5	mΩ
I_D	200	A

TO-220AB





Pb-Free RoHS

Part ID	Package Type	Marking	Tape and reel information
VS40200AT	TO-220AB	40200AT	50pcs/Tube

Maximum ratings, at T_j=25°C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		40	V
I_S	Diode continuous forward current	T_C=25°C	200	A
I_D	Continuous drain current @V_{GS}=-10V	T_C=25°C	200	A
		T_C=100°C	142	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	800	A
EAS	Avalanche energy, single pulsed ②		390	mJ
P_D	Maximum power dissipation	T_C=25°C	150	W
V_{GS}	Gate-Source voltage		±20	V
T_{STG} T_J	Storage and operating temperature range		-55 to 175	°C
Thermal Characteristics				
$R_{\theta JC}$	Thermal Resistance-Junction to Case		1.0	°C/W
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62.5	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @T_j= 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	40	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=40V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_j=125℃)	V_{DS}=40V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.2	1.8	2.4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=60A	--	2.5	4	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=4.5V, I_D=30A	--	3.5	6	mΩ
Dynamic Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=20V,V_{GS}=0V, f=1MHz	5600	6605	7600	pF
C_{oss}	Output Capacitance		400	550	700	pF
C_{rss}	Reverse Transfer Capacitance		320	440	560	pF
R_g	Gate Resistance	f=1MHz	--	1.9	--	Ω
Q_g	Total Gate Charge	V_{DS}=20V,I_D=30A, V_{GS}=10V	--	109	--	nC
Q_{gs}	Gate-Source Charge		--	30.5	--	nC
Q_{gd}	Gate-Drain Charge		--	42	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=20V, I_D=30A, R_G=3Ω, V_{GS}=10V	--	30	--	nS
t_r	Turn-on Rise Time		--	24	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	45.5	--	nS
t_f	Turn-Off Fall Time		--	16.5	--	nS
Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=30A,V_{GS}=0V	--	0.9	1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=30A, V_{GS}=0V di/dt=500A/μs	--	29	--	nS
Q_{rr}	Reverse Recovery Charge			179		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 29A,V_{GS} =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

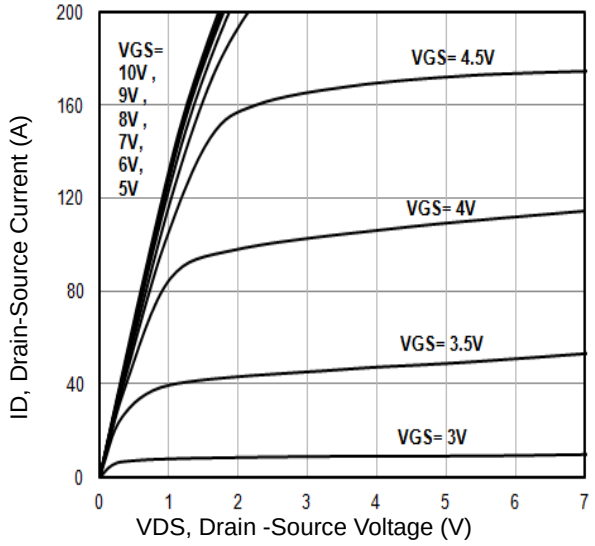


Fig1. Typical Output Characteristics

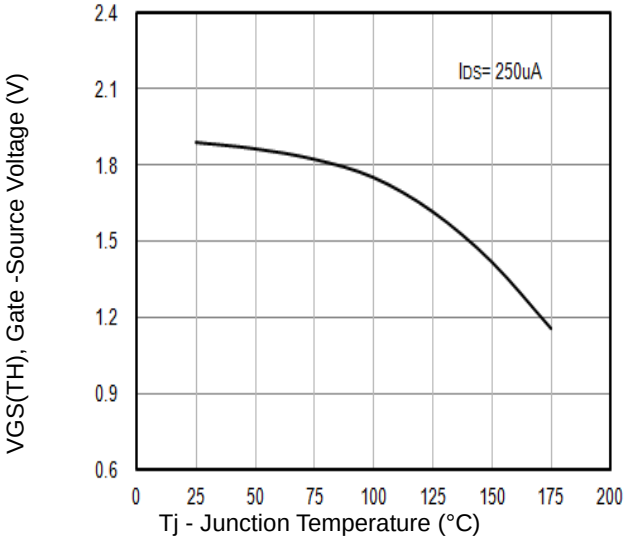


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs.Tj

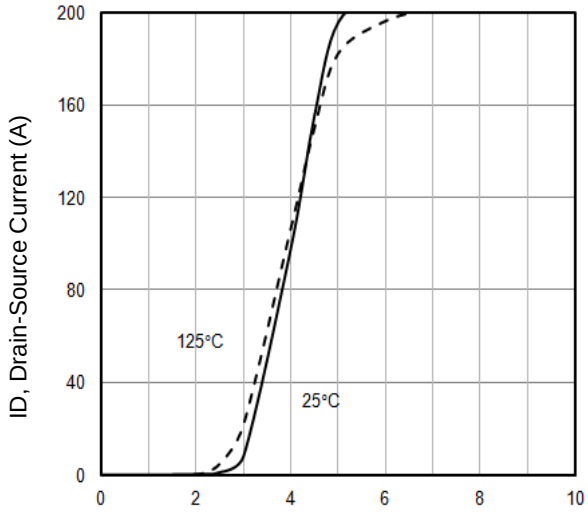


Fig3. Typical Transfer Characteristics

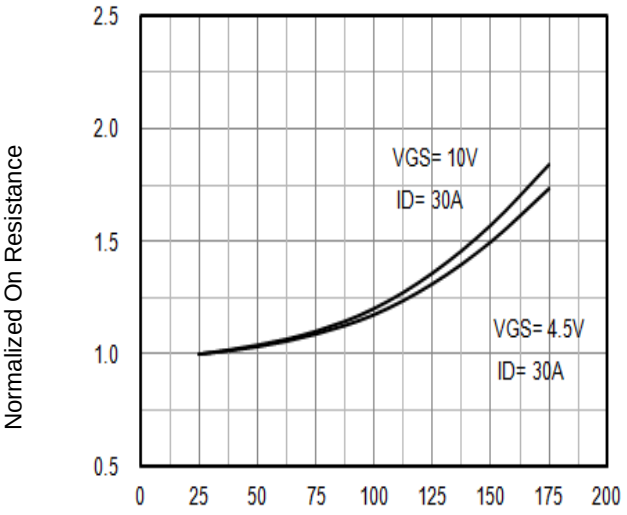


Fig4. Normalized On-Resistance Vs. Tj

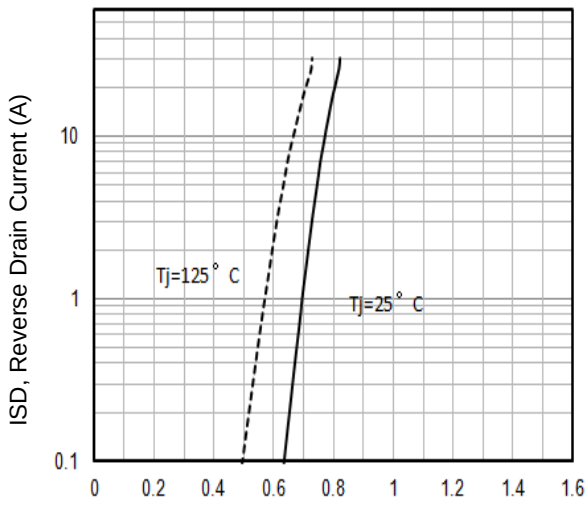


Fig5. Typical Source-Drain Diode Forward Voltage

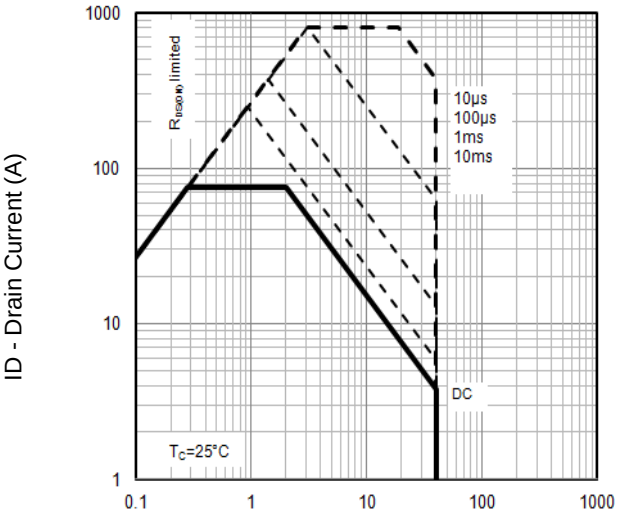


Fig6. Maximum Safe Operating Area

Typical Characteristics

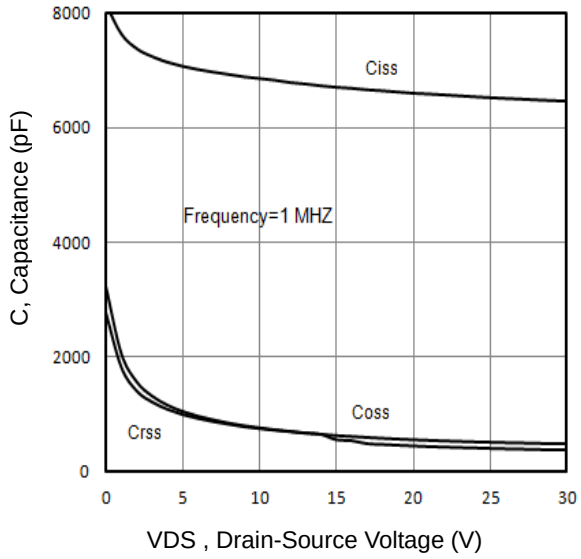


Fig7. Typical Capacitance Vs.Drain-Source Voltage

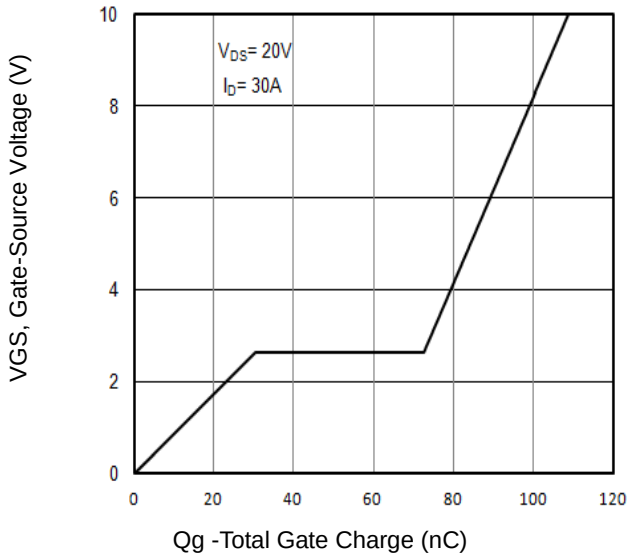


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

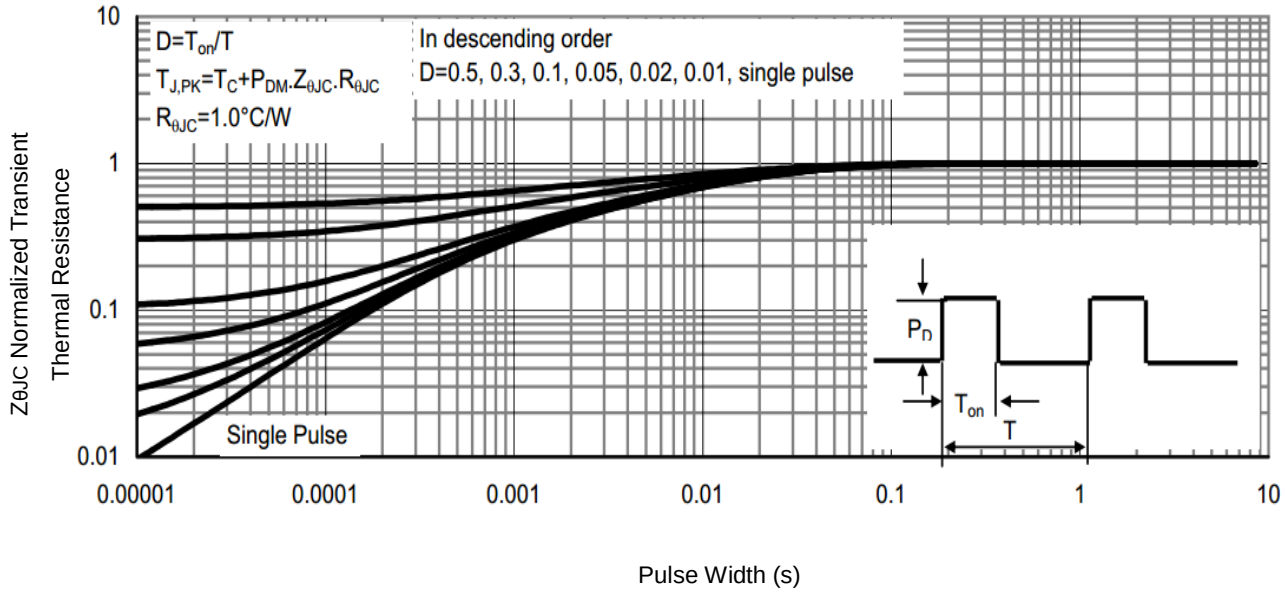


Fig9. Normalized Maximum Transient Thermal Impedance

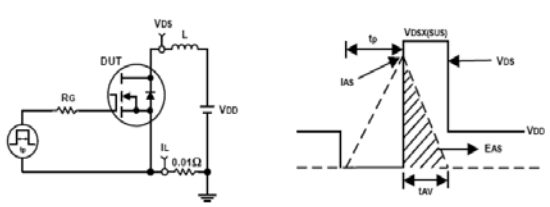


Fig10. Unclamped Inductive Test Circuit and waveforms

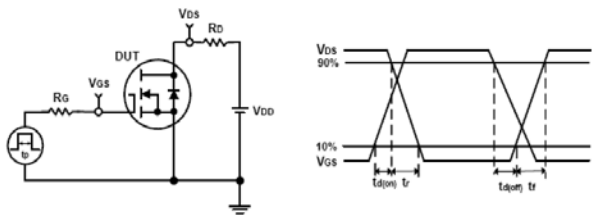
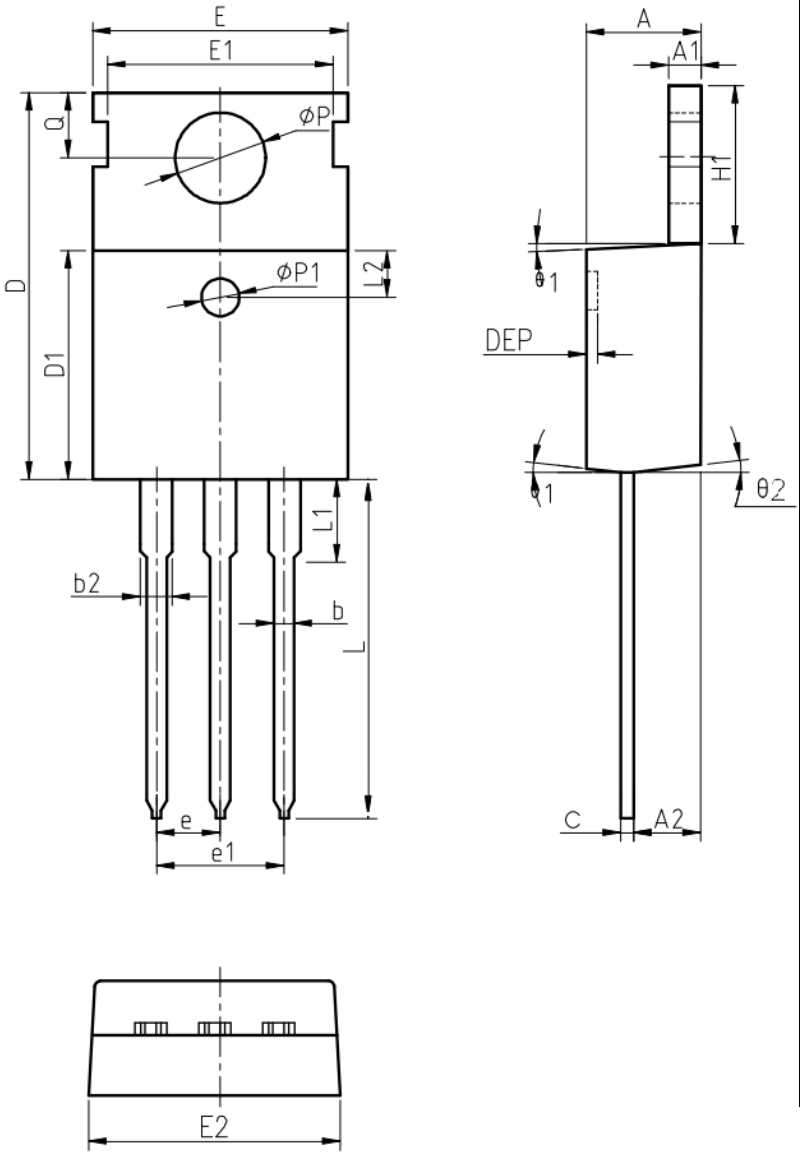


Fig11. Switching Time Test Circuit and waveforms

TO-220AB Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	4.30	4.52	4.70
A1	1.15	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	1.00
b2	1.17	1.32	1.50
c	0.45	0.50	0.61
D	15.30	15.65	15.90
D1	9.00	9.20	9.40
DEP	0.05	0.10	0.25
E	9.66	9.90	10.28
E1	-	8.70	-
E2	9.80	10.00	10.20
ΦP1	1.40	1.50	1.60
e	2.54 BSC		
e1	5.08 BSC		
H1	6.40	6.50	6.80
L	12.70	-	14.27
L1	-	-	3.95
L2	2.40	2.50	2.60
ΦP	3.53	3.60	3.70
Q	2.70	2.80	2.90
θ1	5 °	7 °	9 °
θ2	1 °	3 °	5 °

Notes:

1. Refer to JEDEC TO-220 variation AB
2. Dimension "D" and "E" do NOT include mold flash. Mold flash shall not exceed 0.127mm per side.

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